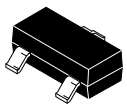
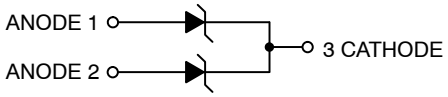
Zener Diodes, 40 Watt Peak Power

SOT-23 Dual Common Cathode Zeners

MMBZxxVxL, SZMMBZxxVxL Series



SOT-23
CASE 318
STYLE 9



These dual monolithic silicon zener diodes are designed for applications requiring protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common cathode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

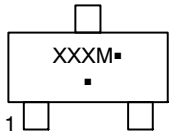
Specification Features:

- SOT-23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Standard Zener Breakdown Voltage Range – 15 V, 27 V, 39 V
- Peak Power – 40 W @ 1.0 ms (Bidirectional), per Figure 5 Waveform
- ESD Rating of Class 3B (exceeding 16 kV) per the Human Body Model
- ESD Rating of IEC61000-4-2 Level 4, ±30 kV Contact Discharge
- Low Leakage < 100 nA
- Flammability Rating: UL 94 V-O
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic case
FINISH: Corrosion resistant finish, easily solderable
MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:
260 °C for 10 Seconds

MARKING DIAGRAM



XXX = 15D, 27C or 39C
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 1.0 ms (Note 1) @ $T_L \le 25$ °C	P_{pk}	40	Watts
Total Power Dissipation on FR-5 Board (Note 2) @ $T_A = 25$ °C Derate above 25 °C	P_D	 225 1.8	 mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Power Dissipation on Alumina Substrate (Note 3) @ $T_A = 25$ °C Derate above 25 °C	P_D	 300 2.4	 mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	− 55 to +150	°C
Lead Solder Temperature − Maximum (10 Second Duration)	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

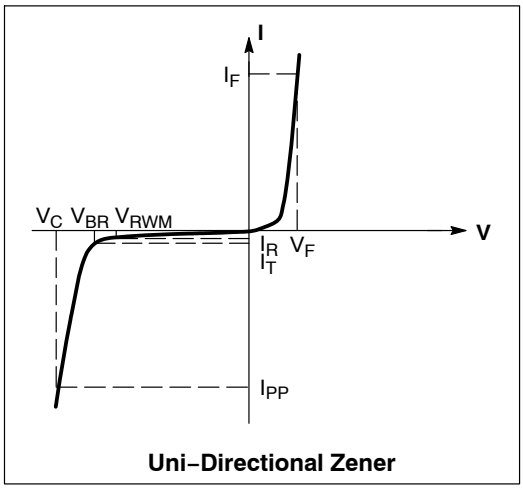
1. Nonrepetitive current pulse per Figure 5 and derate above $T_A = 25$ °C per Figure 6.
2. FR-5 = 1.0 x 0.75 x 0.62 in.
3. Alumina = 0.4 x 0.3 x 0.024 in., 99.5% alumina

ELECTRICAL CHARACTERISTICS

($T_A = 25$ °C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
V_{BR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F



Uni−Directional Zener

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ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)
UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

(V_F = 0.9 V Max @ I_F = 10 mA)

Device*	V_{RWM}	I_R @ V_{RWM}	Breakdown Voltage				V_C @ I_{PP} (Note 6)		V_{BR}
			V_{BR} (Note 5) (V)			@ I_T	V_C	I_{PP}	
	Volts	nA	Min	Nom	Max	mA	V	A	mV/°C
MMBZ15VDL	12.8	100	14.3	15	15.8	1.0	21.2	1.9	12

(V_F = 1.1 V Max @ I_F = 200 mA)

Device*	V_{RWM}	I_R @ V_{RWM}	Breakdown Voltage				V_C @ I_{PP} (Note 6)		V_{BR}
			V_{BR} (Note 5) (V)			@ I_T	V_C	I_{PP}	
	Volts	nA	Min	Nom	Max	mA	V	A	mV/°C
MMBZ27VCL	22	50	25.65	27	28.35	1.0	38	1.0	26

DISCONTINUED (Note 4)

MMBZ39VCLT1G/T3G	31.2	50	37.05	39	40.95	1.0	55	0.76	35.3

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

* Include SZ-prefix devices where applicable.

4. **DISCONTINUED:** These devices are not available. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.
5. V_{BR} measured at pulse test current I_T at an ambient temperature of 25 °C.
6. Surge current waveform per Figure 5 and derate per Figure 6

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TYPICAL CHARACTERISTICS

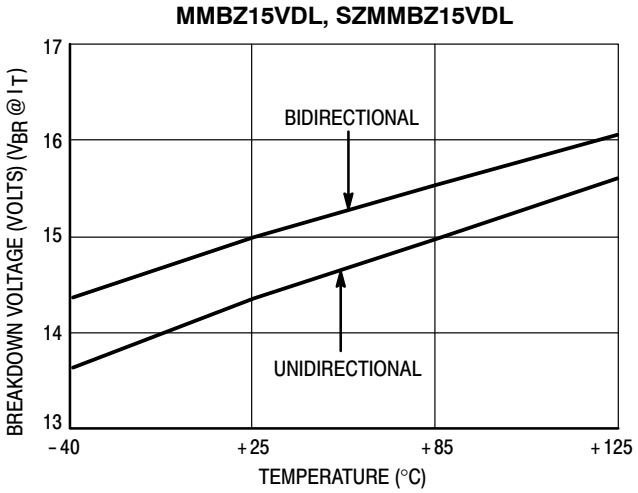


Figure 1. Typical Breakdown Voltage versus Temperature

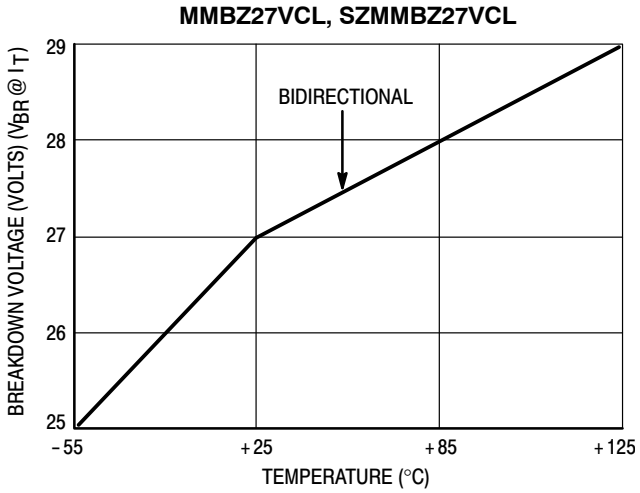


Figure 2. Typical Breakdown Voltage versus Temperature

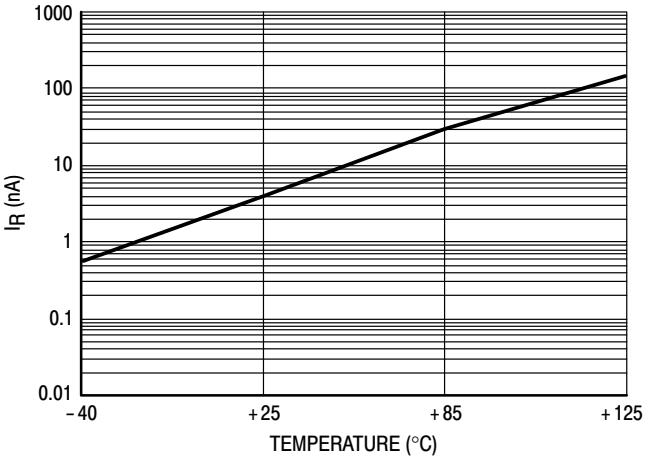


Figure 3. Typical Leakage Current versus Temperature

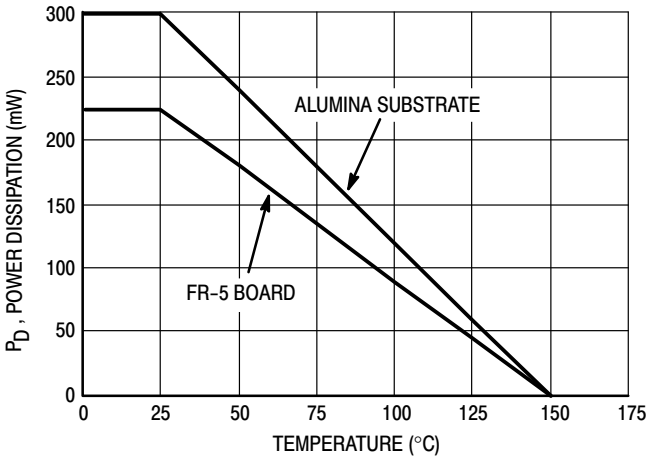


Figure 4. Steady State Power Derating Curve

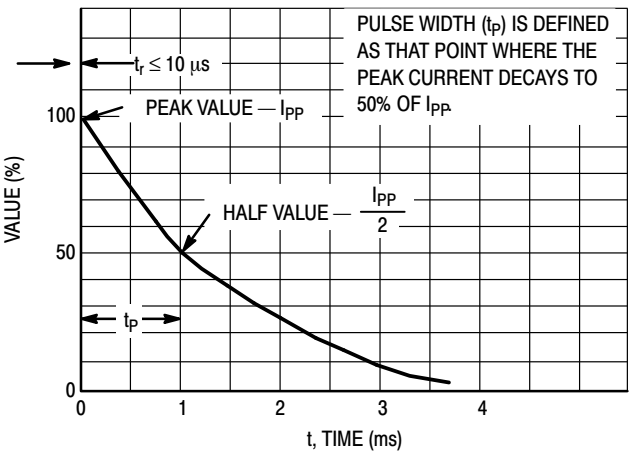


Figure 5. Pulse Waveform

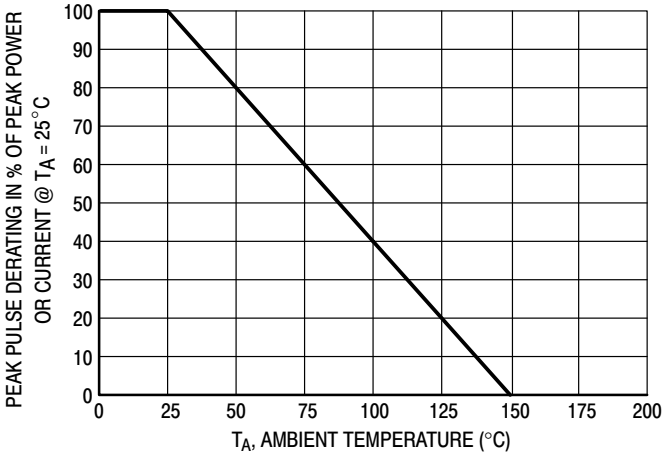
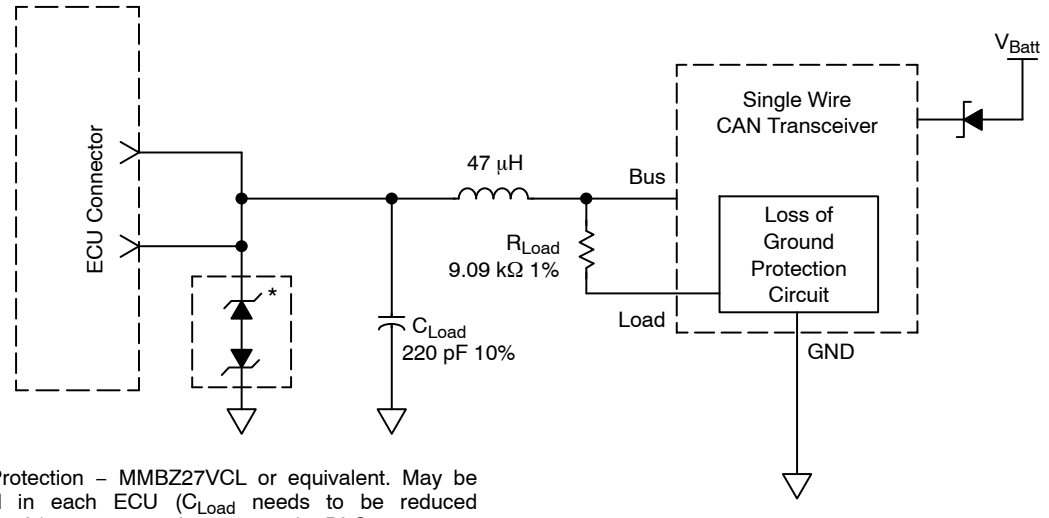


Figure 6. Pulse Derating Curve

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TYPICAL APPLICATIONS



* ESD Protection – MMBZ27VCL or equivalent. May be located in each ECU (C_{Load} needs to be reduced accordingly) or at a central point near the DLC.

Figure 7. Single Wire CAN Network

Figure is the recommended solution for transient EMI/ESD protection. This circuit is shown in the Society of Automotive Engineers February, 2000 J2411 “Single Wire CAN Network for Vehicle Applications” specification (Figure 6). Note: the dual common anode zener configuration shown above is electrically equivalent to a dual common cathode zener configuration.

ORDERING INFORMATION

Device	Specific Marking Code	Package	Shipping†
MMBZ15VDLT1G MMBZ15VDLT1G-NC SZMMBZ15VDLT1G* SZMMBZ15VDLT1G-NC*	15D	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBZ15VDLT3G MMBZ15VDLT3G-NC SZMMBZ15VDLT3G* SZMMBZ15VDLT3G-NC*			10,000 / Tape & Reel
MMBZ27VCLT1G MMBZ27VCLT1G-NC SZMMBZ27VCLT1G* SZMMBZ27VCLT1G-NC*	27C	SOT-23 (Pb-Free)	3000 / Tape & Reel
SZMMBZ27VCLT3G* SZMMBZ27VCLT3G-NC*			10,000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

* SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

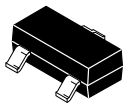
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REVISION HISTORY

Revision	Description of Changes	Date
18	Rebranded the Data Sheet to **onsemi** format. MMBZ39VCLT3G, MMBZ39VCLT1G OPNs Marked as Discontinued.	10/15/2025
19	Added “−NC” OPNs.	9/8/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

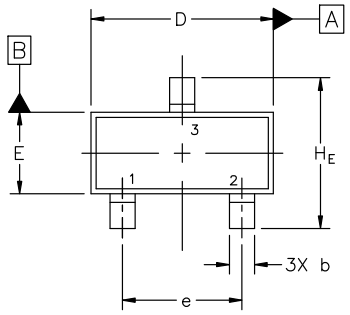
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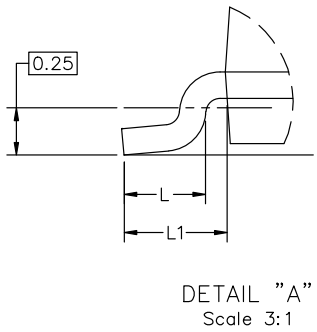
SCALE 4:1

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

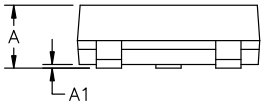
DATE 14 AUG 2024



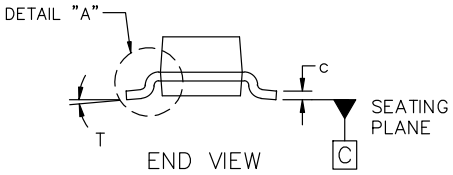
TOP VIEW



DETAIL "A"
Scale 3:1



SIDE VIEW

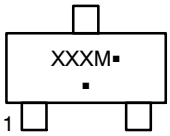


END VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	−−−	10°

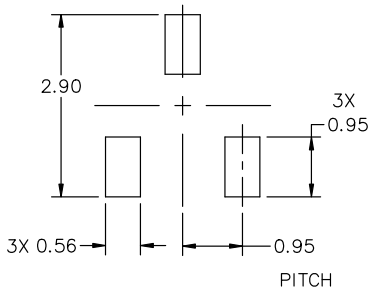
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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DESCRIPTION:	**SOT−23 (TO−236) 2.90x1.30x1.00 1.90P**		**PAGE 1 OF 2**

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CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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